

# Wojciech Knap

## List of Publications by Year in descending order

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451  
papers

12,845  
citations

34493

54  
h-index

33145

104  
g-index

458  
all docs

458  
docs citations

458  
times ranked

7622  
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced terahertz detection of multigate graphene nanostructures. Nanophotonics, 2022, 11, 519-529.	2.9	17
2	Graphene-based plasmonic metamaterial for terahertz laser transistors. Nanophotonics, 2022, 11, 1677-1696.	2.9	15
3	Ultrafast Time-of-Flight Method of Gasoline Contamination Detection Down to ppm Levels by Means of Terahertz Time-Domain Spectroscopy. Applied Sciences (Switzerland), 2022, 12, 1629.	1.3	2
4	Nature of the $1/f$ noise in graphene—direct evidence for the mobility fluctuation mechanism. Nanoscale, 2022, 14, 7242-7249.	2.8	25
5	Terahertz Magnetospectroscopy of Cyclotron Resonances from Topological Surface States in Thick Films of Cd x Hg $1\tilde{x}$ Te. Physica Status Solidi (B): Basic Research, 2021, 258, 2000023.	0.7	8
6	Effect of ultraviolet light on $1/f$ noise in carbon nanotube networks. Materials Research Bulletin, 2021, 134, 111093.	2.7	6
7	Sensitivity of Field-Effect Transistor-Based Terahertz Detectors. Sensors, 2021, 21, 2909.	2.1	54
8	Room temperature depinning of the charge-density waves in quasi-two-dimensional 1T-TaS <sub>2</sub> devices. Applied Physics Letters, 2021, 118, .	1.5	15
9	Double-Quantum-Well AlGaIn/GaN Field Effect Transistors with Top and Back Gates: Electrical and Noise Characteristics. Micromachines, 2021, 12, 721.	1.4	1
10	Roadmap of Terahertz Imaging 2021. Sensors, 2021, 21, 4092.	2.1	143
11	Generation-recombination and $1/f$ noise in carbon nanotube networks. Applied Physics Letters, 2021, 118, .	1.5	8
12	Beatings of ratchet current magneto-oscillations in GaN-based grating gate structures: Manifestation of spin-orbit band splitting. Physical Review B, 2021, 104, .	1.1	10
13	All-Electronic Emitter-Detector Pairs for 250 GHz in Silicon. Sensors, 2021, 21, 5795.	2.1	14
14	Terahertz Sources Based on Emission from a $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll" \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \rangle \text{Ga} \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \text{As} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \rangle$		

#	ARTICLE	IF	CITATIONS
19	THz ratchet effect in HgTe-based lateral superlattices. , 2021, , .		0
20	Review of methods for performance evaluation of antenna-coupled THz detectors. , 2021, , .		0
21	252-GHz Compact All-Electronic CMOS Optopair with SNR of 62 dB. , 2021, , .		0
22	THz photocurrent magneto-oscillations in GaN-based asymmetric grating gate structures. , 2021, , .		0
23	Paving the Way for Tunable Graphene Plasmonic THz Amplifiers. <i>Frontiers in Physics</i> , 2021, 9, .	1.0	10
24	Quantum-Dot Single-Electron Transistors as Thermoelectric Quantum Detectors at Terahertz Frequencies. <i>Nano Letters</i> , 2021, 21, 8587-8594.	4.5	11
25	Graphene/AlGaIn/GaN RF Switch. <i>Micromachines</i> , 2021, 12, 1343.	1.4	8
26	Characterization of Silver Nanowire Layers in the Terahertz Frequency Range. <i>Materials</i> , 2021, 14, 7399.	1.3	1
27	Self-damping of the relaxation oscillations in miniature pulsed transmitter for sub-nanosecond-precision, long-distance LIDAR. <i>Results in Physics</i> , 2020, 19, 103509.	2.0	1
28	Graphene as a Schottky Barrier Contact to AlGaIn/GaN Heterostructures. <i>Materials</i> , 2020, 13, 4140.	1.3	13
29	Quantum Hall states in inverted HgTe quantum wells probed by transconductance fluctuations. <i>Physical Review B</i> , 2020, 102, .	1.1	1
30	Radiation from shallow oxygen impurity in AlGaIn/GaN HEMT structures in magnetic field. <i>Solid State Communications</i> , 2020, 320, 114019.	0.9	1
31	Many-particle effects in optical transitions from zero-mode Landau levels in HgTe quantum wells. <i>Physical Review B</i> , 2020, 102, .	1.1	3
32	AlGaIn/GaN on SiC Devices without a GaN Buffer Layer: Electrical and Noise Characteristics. <i>Micromachines</i> , 2020, 11, 1131.	1.4	19
33	Graphene Epoxy-Based Composites as Efficient Electromagnetic Absorbers in the Extremely High-Frequency Band. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 28635-28644.	4.0	53
34	A 300 GHz Data Communication Receiver Using Plasma-Wave FET Detector in 65nm CMOS. , 2020, , .		2
35	Symmetry breaking and circular photogalvanic effect in epitaxial $\text{CdMnTe}$ films. <i>Physical Review Materials</i> , 2020, 4, .	2.1	21
36	Room-Temperature Amplification of Terahertz Radiation by Grating-Gate Graphene Structures. <i>Physical Review X</i> , 2020, 10, .	2.8	43

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37	Terahertz gain and amplification in current-driven metasurfaces of graphene Dirac plasmons. , 2020, , .		1
38	Silicon based resonant power detector for 620 GHz. , 2020, , .		4
39	Current-driven optical response of plasmonic crystal: From dissipation to amplification. , 2020, , .		0
40	Sub-terahertz detection by fin-shaped GaN/AlGaIn transistors. , 2020, , .		0
41	Anomalous sub-THz detection by GaN/AlGaIn FinFETs. , 2020, , .		0
42	AlGaIn/GaN HEMTs for THz Plasma Wave Detection and Emission. , 2020, , .		2
43	Terahertz Technologies and Applications. , 2019, , .		1
44	Suppressed Auger scattering and tunable light emission of Landau-quantized massless Kane electrons. Nature Photonics, 2019, 13, 783-787.	15.6	23
45	Magneto-transport in inverted HgTe quantum wells. Npj Quantum Materials, 2019, 4, .	1.8	16
46	Time Resolution and Dynamic Range of Field-Effect Transistor-Based Terahertz Detectors. Journal of Infrared, Millimeter, and Terahertz Waves, 2019, 40, 703-719.	1.2	11
47	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. JETP Letters, 2019, 109, 96-101.	0.4	4
48	Massless Dirac fermions in III-V semiconductor quantum wells. Physical Review B, 2019, 99, .	1.1	14
49	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. Condensed Matter, 2019, 4, 27.	0.8	5
50	Terahertz Digital Holography Using Field-Effect Transistor Detectors. , 2019, , .		1
51	Time Resolution and Power Dependence of Transistor Based Terahertz Detectors. , 2019, , .		0
52	About 250/285 GHz push-push oscillator using differential gate equalisation in digital 65-nm CMOS. IET Microwaves, Antennas and Propagation, 2019, 13, 2073-2080.	0.7	2
53	Low frequency noise and trap density in GaN/AlGaIn field effect transistors. Applied Physics Letters, 2019, 115, .	1.5	27
54	Electrical and Noise Characteristics of Fin-Shaped GaN/AlGaIn Devices for High Frequency Operation. , 2019, , .		3

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55	AlGaIn/GaN field effect transistor with two lateral Schottky barrier gates towards resonant detection in sub-mm range. Semiconductor Science and Technology, 2019, 34, 024002.	1.0	15
56	Terahertz light amplification of stimulated emission of radiation in current-injection graphene channel transistor. , 2019, , .		0
57	Temperature-Induced Topological Phase Transition in HgTe Quantum Wells. Physical Review Letters, 2018, 120, 086401.	2.9	43
58	Indium antimonide detector for spectral characterization of terahertz sources. Journal of Applied Physics, 2018, 123, .	1.1	10
59	Electrically controlled wire-channel GaN/AlGaIn transistor for terahertz plasma applications. Applied Physics Letters, 2018, 112, .	1.5	12
60	Spectroscopy of Temperature-Driven Single Valley Dirac Fermions in HgTe/CdHgTe Quantum Wells. , 2018, , .		0
61	Terahertz Light Amplification by Instability-Driven Stimulated Emission of Graphene Plasmon Polaritons. , 2018, , .		1
62	Terahertz InP DHBT-Based Detectors for Studies of Water Status of Sorghum Leaves. , 2018, , .		0
63	AlGaIn/GaN Field Effect Transistors Based on Lateral Schottky Barrier Gates as Millimeter Wave Detectors. , 2018, , .		1
64	Emerging terahertz technologies for security, quality control, vision and medical applications. , 2018, , .		0
65	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. Sensors, 2018, 18, 4341.	2.1	4
66	Graphene ballistic rectifiers for THz detection and imaging. , 2018, , .		1
67	InP double heterojunction bipolar transistors for terahertz computed tomography. AIP Advances, 2018, 8, 085320.	0.6	1
68	Towards wireless THz communications: Photonic-driven source and transistor-based detector. , 2018, , .		0
69	THz detectors based on Si-CMOS technology field effect transistors – advantages, limitations and perspectives for THz imaging and spectroscopy. Opto-electronics Review, 2018, 26, 261-269.	2.4	10
70	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	1.1	24
71	Millimetre band detectors based on GaN/AlGaIn HEMT. , 2018, , .		2
72	Towards resonant THz detector: Devices based on Schottky diodes to 2DEG GaN/AlGaIn. , 2018, , .		0

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73	Terahertz vision using field effect transistors detectors arrays. , 2018, , .		7
74	Millimeter and submillimeter range detector based on graphene ballistic rectifiers. , 2018, , .		3
75	Terahertz Light Amplification by Current-Driven Plasmon Instabilities in Graphene. , 2018, , .		1
76	Graphene-Channel-Transistor Terahertz Amplifier. , 2018, , .		0
77	Band splitting in $\text{HgCdTe}$ quantum wells measured by magnetotransport. Physical Review B, 2018, 97, .	1.3	8
78	Magnetoconductivity of a Mercury Cadmium Telluride Resonant THz Detector. Acta Physica Polonica A, 2018, 134, 973-977.	0.2	1
79	Geometrical Aberration Suppression for Large Aperture Sub-THz Lenses. Journal of Infrared, Millimeter, and Terahertz Waves, 2017, 38, 347-355.	1.2	8
80	Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells. Semiconductors, 2017, 51, 38-42.	0.2	3
81	HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, .	2.2	49
82	Terahertz Detection and Imaging Using Graphene Ballistic Rectifiers. Nano Letters, 2017, 17, 7015-7020.	4.5	100
83	THz imaging and wireless communication using nanotransistor based detectors: From basic physics to first real world applications. , 2017, , .		2
84	THz Beam Shaper Realizing Fan-Out Patterns. Journal of Infrared, Millimeter, and Terahertz Waves, 2017, 38, 1019-1030.	1.2	11
85	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. Physical Review B, 2017, 96, .	1.1	38
86	Detection of high intensity THz radiation by InP double heterojunction bipolar transistors. , 2017, , .		1
87	High-Speed InP-Based double heterojunction bipolar transistors and varactors for three-dimensional terahertz computed tomography. , 2017, , .		1
88	Determination of the sub-terahertz attenuation of brownout clouds generated by rotorcraft. , 2017, , .		2
89	Terahertz probing of temperature-driven topological phase transition in HgCdTe bulk crystal and HgTe Quantum Well. , 2017, , .		0
90	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs "Three-Layer" Gapless Quantum Wells. JETP Letters, 2017, 106, 727-732.	0.4	5

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91	Reducing noise equivalent power in InP DHBT terahertz detector by biasing the collector. , 2017, , .		1
92	Noise limitations of GaN lateral Schottky diodes for THz applications. , 2017, , .		0
93	Temperature-driven massless fermions in HgCdTe heterostructures. , 2017, , .		0
94	Terahertz 3D printed diffractive lens matrices for field-effect transistor detector focal plane arrays. Optics Express, 2016, 24, 20119.	1.7	22
95	GaN/AlGaIn based transistors for terahertz emitters and detectors. , 2016, , .		2
96	Heterostructured hBN $\epsilon$ BP $\epsilon$ hBN Nanodetectors at Terahertz Frequencies. Advanced Materials, 2016, 28, 7390-7396.	11.1	85
97	Observation of topological phase transition by terahertz photoconductivity in HgTe $\epsilon$ based transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 534-537.	0.8	2
98	Pressure- and temperature-driven phase transitions in HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	57
99	Wide modulation bandwidth terahertz detection in 130 nm CMOS technology. EPJ Applied Physics, 2016, 76, 20101.	0.3	7
100	MBE grown GaN/AlGaIn lateral Schottky barrier diodes for high frequency applications. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	0.6	12
101	Surface Leakage Currents in SiN and Al <sub>2</sub> O <sub>3</sub> Passivated AlGaIn/GaN High Electron Mobility Transistors. Chinese Physics Letters, 2016, 33, 067201.	1.3	1
102	Terahertz imaging with arrays of plasma field effect transistors detectors. , 2016, , .		2
103	Two-dimensional plasmons in lateral carbon nanotube network structures and their effect on the terahertz radiation detection. Journal of Applied Physics, 2016, 120, 044501.	1.1	18
104	Temperature-driven massless Kane fermions in HgCdTe crystals. , 2016, , .		2
105	High-Speed Room Temperature Terahertz Detectors Based on InP Double Heterojunction Bipolar Transistors. International Journal of High Speed Electronics and Systems, 2016, 25, 1640011.	0.3	13
106	Imaging and Gas Spectroscopy for Health Protection in Sub-THz Frequency Range. International Journal of High Speed Electronics and Systems, 2016, 25, 1640017.	0.3	3
107	Terahertz cyclotron emission from HgCdTe bulk films. , 2016, , .		0
108	Low frequency noise in two-dimensional lateral GaN/AlGaIn Schottky diodes. Applied Physics Letters, 2016, 109, .	1.5	9

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109	Asymmetric devices based on carbon nanotubes as detectors of sub-THz radiation. Journal of Physics: Conference Series, 2016, 741, 012143.	0.3	2
110	THz magnetospectroscopy of double HgTe quantum well. , 2016, , .		0
111	Terahertz imaging of Landau levels in HgTe-based topological insulators. Applied Physics Letters, 2016, 108, .	1.5	13
112	Black phosphorus and hybrid van der wall heterostructured terahertz photodetectors. , 2016, , .		1
113	Saturation of photoresponse to intense THz radiation in AlGaIn/GaN HEMT detector. Journal of Applied Physics, 2016, 120, 164507.	1.1	14
114	GaN/AlGaIn lateral Schottky barrier diodes for high frequency applications. , 2016, , .		0
115	Substrate optimization for a planar antenna of terahertz Si field effect transistor detectors. , 2016, , .		1
116	Terahertz imaging by field effect transistors. , 2016, , .		0
117	Terahertz imaging with GaAs and GaN plasma field effect transistors detectors. , 2016, , .		4
118	Lateral Schottky barrier diodes based on GaN/AlGaIn 2DEG for sub-THz detection. , 2016, , .		3
119	Terahertz detection by AlGaIn/GaN HEMTs at high intensity. , 2016, , .		1
120	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538.	0.2	9
121	Temperature-driven massless Kane fermions in HgCdTe crystals. Nature Communications, 2016, 7, 12576.	5.8	73
122	Efficient Terahertz detection in black-phosphorus nano-transistors with selective and controllable plasma-wave, bolometric and thermoelectric response. Scientific Reports, 2016, 6, 20474.	1.6	117
123	Phase transitions in two tunnel-coupled HgTe quantum wells: Bilayer graphene analogy and beyond. Scientific Reports, 2016, 6, 30755.	1.6	42
124	Temperature-dependent magnetospectroscopy of HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	21
125	Diffraction optics for GaN terahertz detectors arrays. , 2016, , .		1
126	Performance evaluation of active sub-Terahertz systems in Degraded Visual Environments (DVE). Proceedings of SPIE, 2016, , .	0.8	6



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127	Improvement of terahertz field effect transistor detectors by substrate thinning and radiation losses reduction. Optics Express, 2016, 24, 272.	1.7	39
128	Plasma-Wave Terahertz Detection Mediated by Topological Insulators Surface States. Nano Letters, 2016, 16, 80-87.	4.5	131
129	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. Semiconductors, 2015, 49, 1627-1633.	0.2	6
130	Terahertz studies of 2D and 3D topological transitions. Journal of Physics: Conference Series, 2015, 647, 012037.	0.3	0
131	Response of Graphene Based Gated Nanodevices Exposed to THz Radiation. EPJ Web of Conferences, 2015, 103, 10003.	0.1	1
132	Silicon junctionless field effect transistors as room temperature terahertz detectors. Journal of Applied Physics, 2015, 118, .	1.1	31
133	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. Applied Physics Letters, 2015, 107, .	1.5	13
134	InP Double Heterojunction Bipolar Transistor for broadband terahertz detection and imaging systems. Journal of Physics: Conference Series, 2015, 647, 012036.	0.3	8
135	Black Phosphorus Terahertz Photodetectors. Advanced Materials, 2015, 27, 5567-5572.	11.1	269
136	Non-trivial Berry phase in the Cd <sub>3</sub> As <sub>2</sub> 3D Dirac semimetal. Journal of Physics: Conference Series, 2015, 647, 012064.	0.3	8
137	Terahertz excitations in HgTe-based field effect transistors. Journal of Physics: Conference Series, 2015, 647, 012009.	0.3	0
138	Characterization of integrated antenna-coupled plasma-wave detectors with wide bandwidth amplification in 130nm CMOS. , 2015, , .		4
139	Plasmonic detection of wide band modulated THz radiations in GaAs technology. , 2015, , .		0
140	Cyclotron resonance in InAs/AlSb quantum wells in magnetic fields up to 45 T. Semiconductors, 2015, 49, 1616-1622.	0.2	0
141	Experimental and theoretical investigations of the responsivity of field effect transistors based Terahertz detectors versus substrate thickness. , 2015, , .		1
142	Broadband characteristics of ultrahigh responsivity of asymmetric dual-grating-gate plasmonic terahertz detectors. , 2015, , .		1
143	Improvement of terahertz imaging using lock-in techniques. , 2015, , .		0
144	InP double heterojunction bipolar transistor for detection above 1 THz. , 2015, , .		1

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145	3D printed flat optics and InP heterojunction bipolar transistor based-detector for THz imaging. , 2015, , .		2
146	One dimensional semiconductor nanostructures: An effective <i>active</i>-material for terahertz detection. APL Materials, 2015, 3, .	2.2	17
147	Ultra-broadband near-field antenna for terahertz plasmonic applications. Semiconductors, 2015, 49, 104-108.	0.2	3
148	3-D-Printed Flat Optics for THz Linear Scanners. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 314-316.	2.0	41
149	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. JETP Letters, 2015, 100, 790-794.	0.4	26
150	Room-temperature zero-bias plasmonic THz detection by asymmetric dual-grating-gate HEMT. Proceedings of SPIE, 2015, , .	0.8	0
151	Terahertz magneto-spectroscopy of a point contact based on CdTe/CdMgTe quantum well. Journal of Nanophotonics, 2015, 9, 093082.	0.4	4
152	Terahertz Wave Generation Using Graphene and Compound Semiconductor Nano-Heterostructures. Nanostructure Science and Technology, 2015, , 237-261.	0.1	0
153	AlGaIn/GaN HEMTâ€™s photoresponse to high intensity THz radiation. Opto-electronics Review, 2015, 23, .	2.4	8
154	Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions: A comparison. Journal of Applied Physics, 2015, 117, 112803.	1.1	7
155	Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells. Journal of Applied Physics, 2015, 117, 112813.	1.1	16
156	Mechanism of Hydrogen Sensing by AlGaIn/GaN Pt-Gate Field Effect Transistors: Magnetoresistance Studies. IEEE Sensors Journal, 2015, 15, 123-127.	2.4	5
157	Application of plasma-wave detectors for ultra-short pulse terahertz radiation. , 2014, , .		0
158	Detection of terahertz and mid-infrared radiations by InP-based asymmetric dual-grating-gate HEMTs. , 2014, , .		1
159	Terahertz photodetectors based on tapered semiconductor nanowires. Applied Physics Letters, 2014, 105, .	1.5	14
160	Terahertz magnetospectroscopy of a point contact based on CdTe/CdMgTe quantum well. Proceedings of SPIE, 2014, , .	0.8	2
161	InP double heterojunction bipolar transistor as sub-terahertz detector. , 2014, , .		1
162	Terahertz wireless communication using GaAs transistors as detectors. Electronics Letters, 2014, 50, 323-325.	0.5	24

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163	Nanowire Terahertz detectors with a resonant four-leaf-clover-shaped antenna. Optics Express, 2014, 22, 8996.	1.7	17
164	Nonlinear photoresponse of field effect transistors terahertz detectors at high irradiation intensities. Journal of Applied Physics, 2014, 115, .	1.1	36
165	High-performance room-temperature THz nanodetectors with a narrowband antenna. Proceedings of SPIE, 2014, , .	0.8	2
166	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. Nature Physics, 2014, 10, 233-238.	6.5	190
167	Ultrahigh sensitive sub-terahertz detection by InP-based asymmetric dual-grating-gate high-electron-mobility transistors and their broadband characteristics. Applied Physics Letters, 2014, 104, .	1.5	158
168	Detection of high intensity thz radiation by field effect transistors. , 2014, , .		0
169	Analysis of sub-THz radiation detector built of planar antenna integrated with MOSFET. Microelectronics Journal, 2014, 45, 1168-1176.	1.1	14
170	High performance bilayer-graphene terahertz detectors. Applied Physics Letters, 2014, 104, .	1.5	149
171	Sub-terahertz photoconductivity of Hg <sub>x</sub> Cd <sub>1-x</sub> Te crystals with composition close to semiconductor-to-semimetal topological transition. , 2014, , .		0
172	Recent Results on Broadband Nanotransistor Based THz Detectors. NATO Science for Peace and Security Series B: Physics and Biophysics, 2014, , 189-209.	0.2	5
173	Generation of THz radiation due to 2D-plasma oscillations in interdigitated GaN quantum well structures at room temperature. Lithuanian Journal of Physics, 2014, 54, 58-62.	0.1	1
174	Terahertz Plasma Field Effect Transistors. Springer Series in Optical Sciences, 2014, , 77-100.	0.5	4
175	Nanowire-based field effect transistors for terahertz detection and imaging systems. Nanotechnology, 2013, 24, 214005.	1.3	40
176	InP- and GaAs-Based Plasmonic High-Electron-Mobility Transistors for Room-Temperature Ultrahigh-Sensitive Terahertz Sensing and Imaging. IEEE Sensors Journal, 2013, 13, 89-99.	2.4	69
177	Nanometer size field effect transistors for terahertz detectors. Nanotechnology, 2013, 24, 214002.	1.3	80
178	Field effect transistor as detector of THz radiation helicity. , 2013, , .		0
179	The dynamic range of THz broadband FET detectors. , 2013, , .		5
180	Nanotransistor based THz plasma detectors: low temperatures, graphene, linearity, and circular polarization studies. , 2013, , .		2

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181	Plasmonic and bolometric terahertz detection by graphene field-effect transistor. Applied Physics Letters, 2013, 103, 181114.	1.5	66
182	Room temperature generation of THz radiation in GaN quantum wells structures. Proceedings of SPIE, 2013, , .	0.8	0
183	Temperature, back gate and polarization studies in nanotransistor based THz plasma detectors. , 2013, , .		0
184	Signal-to-noise ratio in terahertz wireless communication using field-effect-transistors as detectors. , 2013, , .		1
185	Wireless communication at 310 GHz using GaAs high-electron-mobility transistors for detection. Journal of Communications and Networks, 2013, 15, 559-568.	1.8	37
186	Terahertz detection using Si-SiGe MODFETs. , 2013, , .		0
187	0.2 THz wireless communication using plasma-wave transistor detector. , 2013, , .		7
188	Plasmonic and bolometric terahertz graphene sensors. , 2013, , .		2
189	Terahertz emission and detection using two dimensional plasmons in semiconductor nano-heterostructures for sensing applications. , 2013, , .		0
190	Emission and Detection of Terahertz Radiation Using Two-Dimensional Electrons in III-V Semiconductors and Graphene. IEEE Transactions on Terahertz Science and Technology, 2013, 3, 63-71.	2.0	98
191	Antenna-coupled heterostructure field effect transistors for integrated terahertz heterodyne mixers. , 2013, , .		2
192	Terahertz imaging using strained-Si MODFETs as sensors. Solid-State Electronics, 2013, 83, 113-117.	0.8	16
193	Room-temperature nanowire terahertz photodetectors. Proceedings of SPIE, 2013, , .	0.8	0
194	Performance limits for field effect transistors as terahertz detectors. Applied Physics Letters, 2013, 102, .	1.5	95
195	Asymmetric dual-grating gate InGaAs/InAlAs/InP HEMTs for ultrafast and ultrahigh sensitive terahertz detection. , 2013, , .		0
196	Extremely-high sensitive terahertz detector based on dual-grating gate InP-HEMTs. , 2013, , .		1
197	Emission and detection of terahertz radiation using two dimensional plasmons in semiconductor nano-heterostructures for nondestructive evaluations. Proceedings of SPIE, 2013, , .	0.8	2
198	Plasmonic terahertz monochromatic coherent emission from an asymmetric chirped dual-grating-gate InP-HEMT with a photonic vertical cavity. , 2013, , .		2

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199	Plasmonic Terahertz Monochromatic Coherent Emission from an Asymmetric Chirped Dual-Grating-Gate InP-HEMT with a Photonic Vertical Cavity. , 2013, , .		3
200	Magneto spectroscopy of HgTe based topological insulators. , 2013, , .		0
201	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. Journal of Physics: Conference Series, 2013, 461, 012038.	0.3	1
202	Emission and detection of terahertz radiation using two-dimensional plasmons in semiconductor nanoheterostructures for nondestructive evaluations. Optical Engineering, 2013, 53, 031206.	0.5	29
203	Field effect transistors for terahertz applications. , 2013, , 121-155.		34
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